

Markus H. Neuwirth

# Process Development for Wet Chemical Fabrication of $\text{Cu}_2\text{ZnSn}(\text{S},\text{Se})_4$ Solar Cells

# **Process Development for Wet Chemical Fabrication of Cu<sub>2</sub>ZnSn(S,Se)<sub>4</sub> Solar Cells**

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M.Sc. Markus Hans Neuwirth  
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Referent : Prof. Dr. Heinz Kalt  
Korreferent : Priv.-Doz. Dr. Michael Hetterich

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Prof. Dr. H. Kalt  
Priv.-Doz. Dr. M. Hetterich  
Prof. Dr. M. Le Tacon  
Prof. Dr. C. Rockstuhl  
Prof. Dr. M. Steinhauser



Karlsruher Institut für Technologie (KIT)  
Institut für Angewandte Physik  
Wolfgang-Gaede-Straße 1  
76131 Karlsruhe  
Germany

AG Kalt: <http://www.aph.kit.edu/kalt>

Markus Hans Neuwirth  
[markus.neuwirth@kit.edu](mailto:markus.neuwirth@kit.edu) [neuwirthmarkus@gmail.com](mailto:neuwirthmarkus@gmail.com)

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**Markus H. Neuwirth**

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